



AMERICAN
MICROSEMICONDUCTOR

BAV65 Diodes

General Purpose UHF/MW Mixer Diode

Military/High-Rel N

V(RRM)(V) Rep.Pk.Rev. Voltage

Band

Test Freq 1.0G

Frequency Min. (Hz)

Frequency Max. (Hz)

V(FM) Max.(V) Forward Voltage

Ct{Cj} Nom. (F) Junction Cap.

NR Max.

Noise Figure Max. (dB) 6.5

Maximum Conversion Loss (dB)

I(RM) Max.(A) Reverse Current

Inp VSWR Max.

If Imped. Min

If Imped. Max.

Power In (test)

R(load) (Ohms)

Zm (test)

Burnout Abs Max.

Semiconductor Material Silicon

Maximum Operating Temp (°C)